

### Small Signal Fast Switching Diodes



#### FEATURES

- Silicon epitaxial planar diode
- Automotive graded device
- AEC-Q101 qualified

#### APPLICATIONS

- Extreme fast switches



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

#### MECHANICAL DATA

**Case:** DO-35

**Weight:** approx. 125 mg

**Cathode band color:** black

**Packaging codes/options:**

TR/10K per 13" reel (52 mm tape), 50K/box

TAP/10K per ammpack (52 mm tape), 50K/box

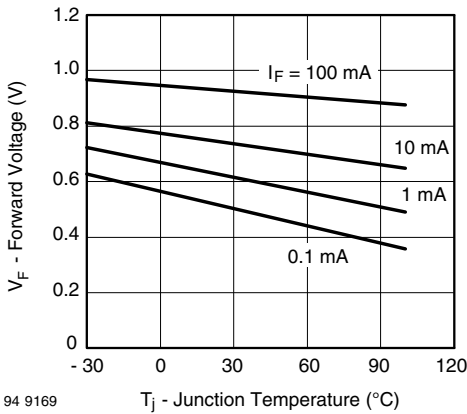
PARTS TABLE				
PART	ORDERING CODE	TYPE MARKING	INTERNAL CONSTRUCTION	REMARKS
1N4148-P	1N4148-P-TAP or 1N4148-P-TR	V4148	Single diode	Tape and reel/ammopack

ABSOLUTE MAXIMUM RATINGS (T <sub>amb</sub> = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Repetitive peak reverse voltage		V <sub>RRM</sub>	100	V
Reverse voltage		V <sub>R</sub>	75	V
Peak forward surge current	t <sub>p</sub> = 1 μs	I <sub>FSM</sub>	2	A
Repetitive peak forward current		I <sub>FRM</sub>	500	mA
Forward continuous current		I <sub>F</sub>	300	mA
Average forward current	V <sub>R</sub> = 0	I <sub>F(AV)</sub>	150	mA
Power dissipation	l = 4 mm, T <sub>L</sub> = 45 °C	P <sub>tot</sub>	440	mW
	l = 4 mm, T <sub>L</sub> ≤ 25 °C	P <sub>tot</sub>	500	mW

THERMAL CHARACTERISTICS (T <sub>amb</sub> = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Thermal resistance junction to ambient air	l = 4 mm, T <sub>L</sub> = constant	R <sub>thJA</sub>	350	K/W
Junction temperature		T <sub>j</sub>	175	°C
Storage temperature range		T <sub>stg</sub>	- 65 to + 150	°C

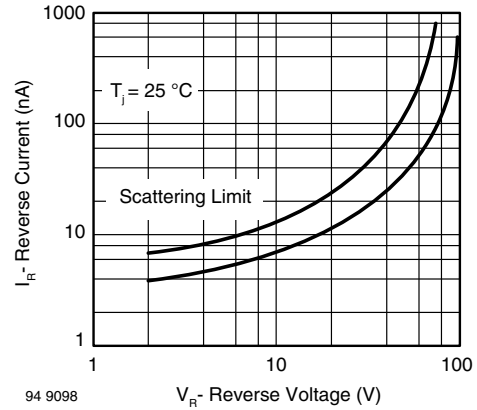
ELECTRICAL CHARACTERISTICS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 10\text{ mA}$	$V_F$			1	V
Reverse current	$V_R = 20\text{ V}$	$I_R$			25	nA
	$V_R = 20\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$	$I_R$			50	$\mu\text{A}$
Reverse current	$V_R = 75\text{ V}$	$I_R$			5	$\mu\text{A}$
	$I_R = 100\text{ }\mu\text{A}, t_p/T = 0.01, t_p = 0.3\text{ ms}$	$V_{(BR)}$	100			V
Diode capacitance	$V_R = 0\text{ V}, f = 1\text{ MHz}, V_{HF} = 50\text{ mV}$	$C_D$			4	pF
Rectification efficiency	$V_{HF} = 2\text{ V}, f = 100\text{ MHz}$	$\eta_r$	45			%
Reverse recovery time	$I_F = I_R = 10\text{ mA}, i_R = 1\text{ mA}$	$t_{rr}$			8	ns
	$I_F = 10\text{ mA}, V_R = 6\text{ V}, i_R = 0.1 \times I_R, R_L = 100\text{ }\Omega$	$t_{rr}$			4	ns

### TYPICAL CHARACTERISTICS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)



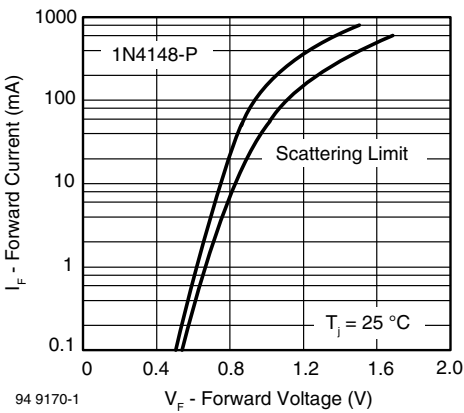
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Fig. 1 - Forward Voltage vs. Junction Temperature



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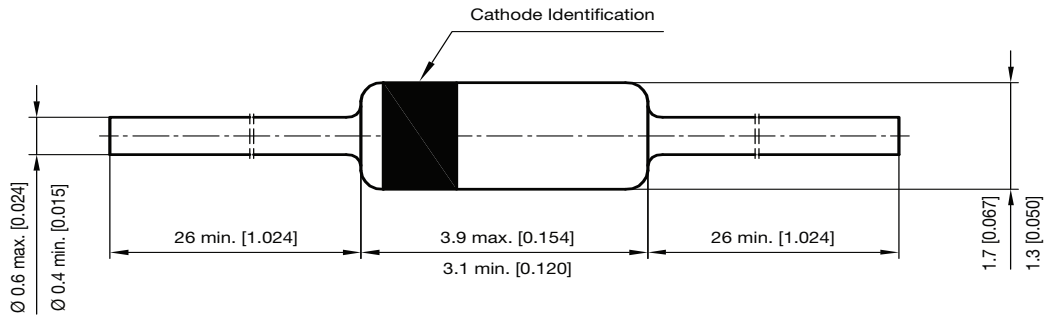
Fig. 3 - Reverse Current vs. Reverse Voltage



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Fig. 2 - Forward Current vs. Forward Voltage

**PACKAGE DIMENSIONS** in millimeters (inches): **DO-35**



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